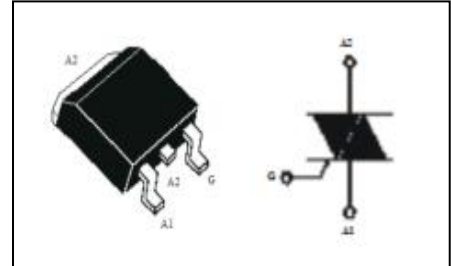


DESCRIPTION

- With TO-263 packaging
- Operating in 3 quadrants
- High commutation capability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation


APPLICATIONS

- Switching applications
- Phase control
- Static switching on inductive or resistive load

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

SYMBOL	PARAMETER	MIN	UNIT
V _{DRM}	Repetitive peak off-state voltage	800	V
V _{RRM}	Repetitive peak reverse voltage	800	V
I _{T(RMS)}	RMS on-state current T _c = 100°C	25	A
I _{TSM}	Non-repetitive peak on-state current	50HZ 190 60HZ 209	A
T _j	Operating junction temperature	-40~125	°C
T _{stg}	Storage temperature	-40~150	°C
R _{th(j-c)}	Thermal resistance (Junction to Case)	1.4	°C/W

ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise specified)

SYMBOL	PARAMETER		CONDITIONS	MAX	UNIT
I _{RRM}	Repetitive peak reverse current		V _{DRM} =V _{RRM} ; T _j =125°C	0.5	mA
I _{DRM}	Repetitive peak off-state current		V _{DRM} =V _{RRM} ; T _j =125°C	0.5	mA
I _{GT}	Gate trigger current	I	V _D =12V; I _T =0.1A	50	mA
		II		50	
		III		50	
V _{GT}	Gate trigger voltage all quadrant		V _D =12V; I _T =0.1A	1.5	V
V _{TM}	On-state voltage		I _{TM} =30A; T _j = 25°C	1.55	V